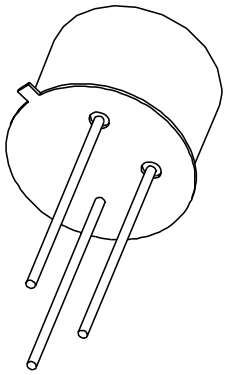
DATA SHEET



BSS61; BSS62
PNP Darlington transistors

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 May 14

Philips
Semiconductors

PHILIPS

PNP Darlington transistors BSS61; BSS62

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V)
- Integrated diode and resistor.

APPLICATIONS

- Industrial high gain amplification.

DESCRIPTION

PNP Darlington transistor in a TO-39 metal package.
NPN complements: BSS51 and BSS52.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case

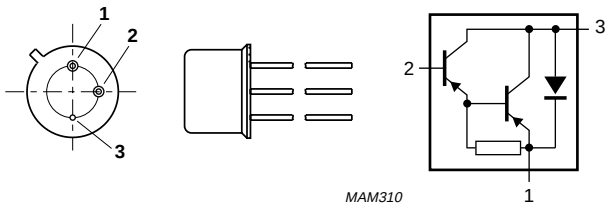


Fig.1 Simplified outline (TO-39) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter				
	BSS61		–	–	–80	V
	BSS62		–	–	–90	V
V_{CES}	collector-emitter voltage	V_{BE} = 0				
	BSS61		–	–	–60	V
	BSS62		–	–	–80	V
I_C	collector current (DC)		–	–	–1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	–	0.8	W
		$T_{case} \leq 25$ °C	–	–	5	W
h_{FE}	DC current gain	I_C = –500 mA; V_{CE} = –10 V	2000	–	–	
f_T	transition frequency	I_C = –500 mA; V_{CE} = –5 V; f = 100 MHz	–	200	–	MHz

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	BSS61		–	–80	V
	BSS62		–	–90	V
V_{CES}	collector-emitter voltage	V_{BE} = 0			
	BSS61		–	–60	V
	BSS62		–	–80	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–1	A
I_{CM}	peak collector current		–	–2	A
I_B	base current (DC)		–	–100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	–	0.8	W
		$T_{case} \leq 25$ °C	–	5	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	200	°C
T_{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	in free air	220	K/W
$R_{th\ j\text{-}c}$	thermal resistance from junction to case		35	K/W

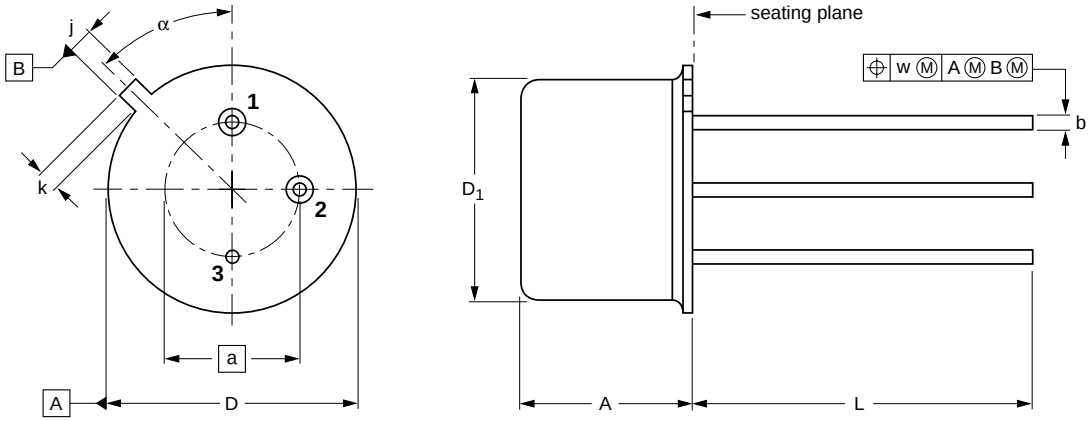
CHARACTERISTICS

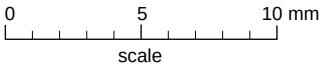
T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	collector cut-off current					
	BSS61	V_{BE} = 0; V_{CE} = –60 V	–	–	–50	nA
	BSS62	V_{BE} = 0; V_{CE} = –80 V	–	–	–50	nA
I_{EBO}	emitter cut-off current	I_C = 0; V_{EB} = –4 V	–	–	–100	nA
h_{FE}	DC current gain	I_C = –150 mA; V_{CE} = –10 V	1000	–	–	
		I_C = –500 mA; V_{CE} = –10 V	2000	–	–	
V_{CEsat}	collector-emitter saturation voltage	I_C = –500 mA; I_B = –0.5 mA	–	–	–1.3	V
		I_C = –500 mA; I_B = –0.5 mA; T_j = 200 °C	–	–	–1.3	V
V_{CEsat}	collector-emitter saturation voltage					
	BSS61	I_C = –1 A; I_B = –1 mA	–	–	–1.6	V
		I_C = –1 A; I_B = –1 mA; T_j = 200 °C	–	–	–1.6	V
V_{CEsat}	collector-emitter saturation voltage					
	BSS62	I_C = –1 A; I_B = –4 mA	–	–	–1.6	V
		I_C = –1 A; I_B = –4 mA; T_j = 200 °C	–	–	–1.6	V
V_{BEsat}	base-emitter saturation voltage	I_C = –500 mA; I_B = –0.5 mA	–	–	–1.9	V
V_{BEsat}	base-emitter saturation voltage					
	BSS61	I_C = –1 A; I_B = –1 mA	–	–	–2.2	V
	BSS62	I_C = –1 A; I_B = –4 mA	–	–	–2.2	V
f_T	transition frequency	I_C = –500 mA; V_{CE} = –5 V; f = 100 MHz	–	200	–	MHz
Switching times (between 10% and 90% levels)						
t_{on}	turn-on time	I_{Con} = –500 mA; I_{Bon} = –0.5 mA; I_{Boff} = 0.5 mA	–	0.5	–	µs
		I_{Con} = –1 A; I_{Bon} = –1 mA; I_{Boff} = 1 mA	–	0.4	–	µs
t_{off}	turn-off time	I_{Con} = –500 mA; I_{Bon} = –0.5 mA; I_{Boff} = 0.5 mA	–	0.7	–	µs
		I_{Con} = –1 A; I_{Bon} = –1 mA; I_{Boff} = 1 mA	–	1.5	–	µs

PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads **SOT5/11**





DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D_1	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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